SKiM 150GD128D

SKiM 4

SPT IGBT Module

SKiM 150GD128D

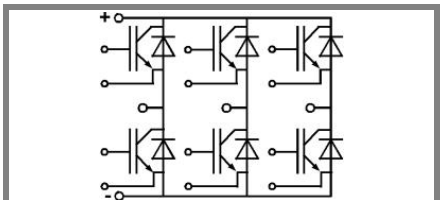
Target Data

Features

- N channel, homogeneous planar IGBT Silicon structure with n+ buffer layer in SPT (soft punch through) technology
- Low inductance case
- Fast & soft inverse CAL diodes
- Isolated by Al2O3 DCB (Direct Copper Bonded) ceramic plate
- Pressure contact technology for thermal contacts
- Spring contyact system to attach driver PCB to the control
- Integrated temperature sensor

Typical Applications

- Switched mode power supplies
- Three phase inverters for AC motor speed control
- Switching (not for linear use)



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Absolute Maximum Ratings	T_{case} = 25°C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
I_C	T_s = 25 (80) °C	110 (80)	A
I_{CRM}	t_p = 1 ms	200	A
V_{GES}		± 20	V
T_j (T_{stg})		-40 ... 150 (125)	°C
T_{cop}	max. case operating temperature	125	°C
V_{isol}	AC, 1 min.	2500	V
Inverse diode			
I_F	T_s = 25 (80) °C	110 (70)	A
I_{FRM}	t_p = 1 ms	200	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	1100	A

Characteristics	T_{case} = 25°C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	V_{GE} = V_{CE}; I_C = 8 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0; V_{CE} = V_{CES}; T_j = 25 (125) °C		0,1	0,3	mA
V_{CEO}	T_j = 25 (125) °C		1 (0,9)	1,15 (1,05)	V
r_{CE}	T_j = 25 (125) °C		9 (12)	12 (15)	mΩ
V_{CEsat}	I_{Cnom} = 100 A; V_{GE} = 15 V, T_j = 25 (125) °C on chip level		1,9 (2,1)	2,35 (2,55)	V
C_{ies}	V_{GE} = 0; V_{CE} = 25 V; f = 1 MHz		9		nF
C_{oes}	V_{GE} = 0; V_{CE} = 25 V; f = 1 MHz		1		nF
C_{res}	V_{GE} = 0; V_{CE} = 25 V; f = 1 MHz		1		nF
L_{CE}				15	nH
$R_{CC'+EE'}$	resistance, terminal-chip T_c= 25 (125) °C		1,35 (1,75)		mΩ
$t_{d(on)}$	V_{CC} = 600 V				ns
t_r	I_{Cnom} = 100 A				ns
$t_{d(off)}$	R_{Gon} = R_{Goff} = Ω				ns
t_f	T_j = 125 °C				ns
E_{on} (E_{off})	V_{GE} ± 15 V		11,5 (9,5)		mJ
E_{on} (E_{off})	with SKHI 64; T_j = 125 °C V_{CC} = 600 V; I_C = 100 A				mJ
Inverse diode					
V_F = V_{EC}	I_{Fnom} = 100 A; V_{GE} = 0 V; T_j = 25 (125) °C		2 (1,8)	2,5 (2,3)	V
V_{TO}	T_j = 25 (125) °C		1,1	1,45 (1,25)	V
r_T	T_j = 25 (125) °C		9	13 (11)	mΩ
I_{RRM}	I_F = 100 A; T_j = 125 °C				A
Q_{rr}	V_{GE} = 0 V di/dt = A/µs				µC
E_{rr}	R_{Gon} = R_{Goff} = Ω				mJ
Thermal characteristics					
$R_{th(j-s)}$	per IGBT			0,4	K/W
$R_{th(j-s)}$	per FWD			0,5	K/W
Temperature Sensor					
R_{TS}	T = 25 (100) °C		1 (6,7)		kΩ
tolerance	T = 25 (100) °C		3 (2)		%
Mechanical data					
M_1	to heatsink (M5)	2		3	Nm
M_2	for terminals (M6)	4		5	Nm
w				310	g

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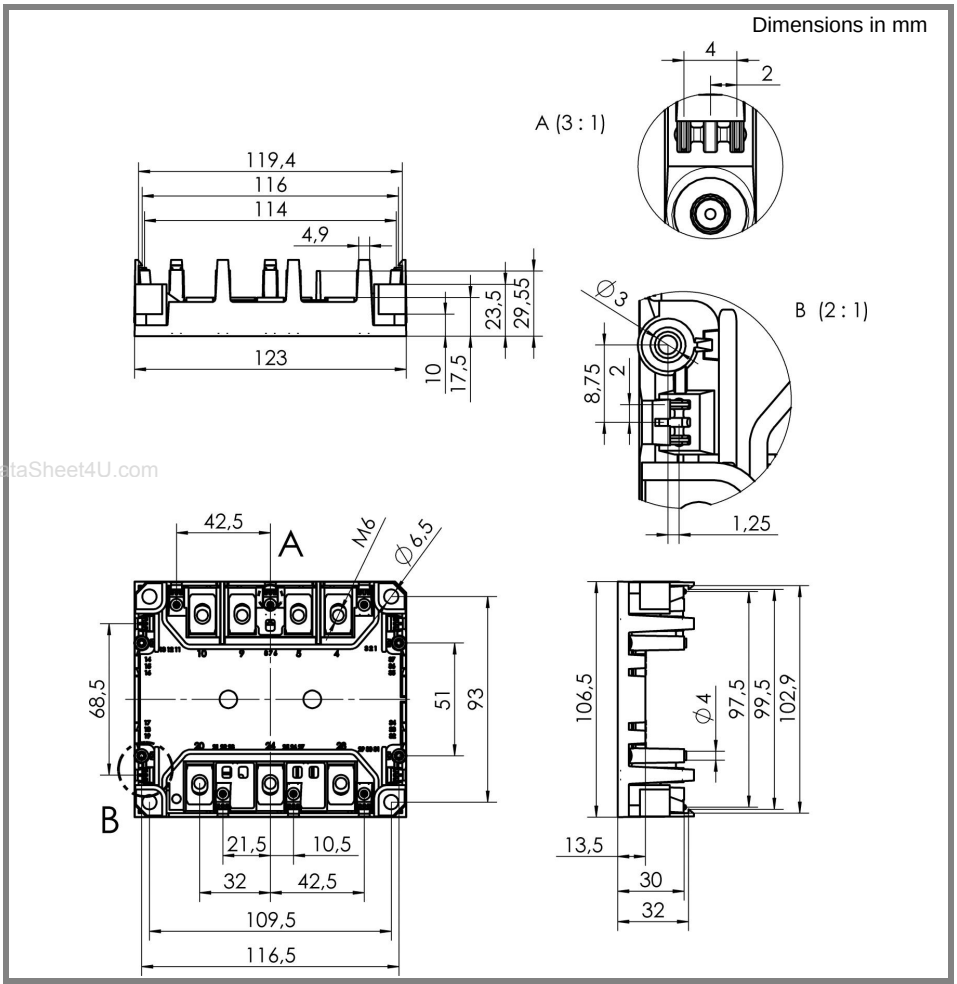
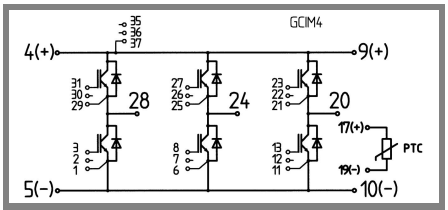


Case SKiM 4



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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